

A cross-sectional view of a semiconductor device. The structure consists of an n-substrate (12) at the base, followed by a buried oxide layer (14). Above the buried oxide is a thermal oxide layer (16). A nitride layer (18) is deposited on top of the thermal oxide. A patterned layer (20) is formed on the nitride, with openings (22) exposing the thermal oxide. A PI (polyimide) layer (24) is deposited over the thermal oxide and nitride. A patterned layer (26) is formed on the PI, with openings (30) exposing the PI. A nitride layer (32) is deposited over the PI. A patterned layer (34) is formed on the nitride, with openings (36) exposing the nitride. A nitride layer (38) is deposited over the patterned layer (34). A patterned layer (40) is formed on the nitride, with openings (42) exposing the nitride. A nitride layer (44) is deposited over the patterned layer (40).

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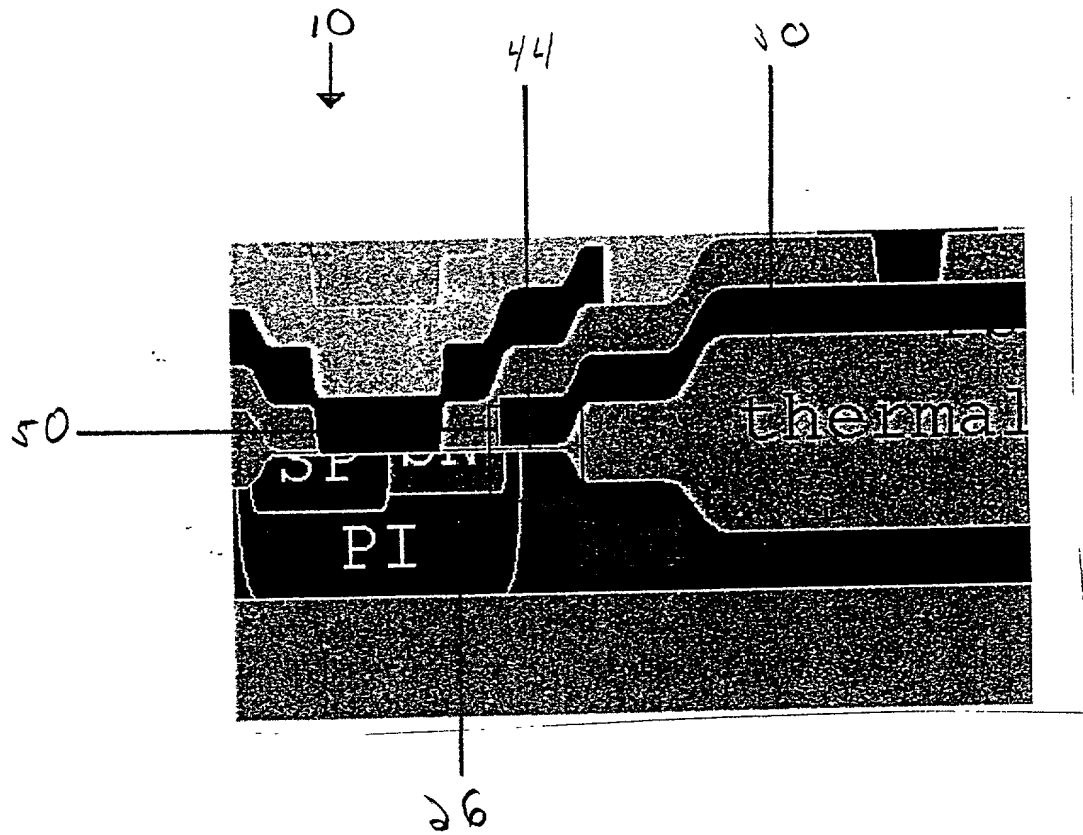


FIG. 2

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